Tim e-controlled charge injection in a quantum Hall uid

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We consider the injection of a controlled charge from a norm almetal into an edge state of the fractional quantum H alle ect, with a time-dependent voltage V (t). Using perturbative calculations in the tunneling limit, and a chiral Luttinger liquid model for the edge state, we show that the electronic correlations prevent the charge uctuations to be divergent for a generic voltage pulse V (t). This is in strong contrast with the case of charge injection in a norm almetal, where this divergence is present. We show that explicit form ull for the mean injected charge and its uctuations can be obtained using an adiabatic approximation, and that non perturbative results can be obtained for injection in an edge state of the FQHE with lling factor = 1=3. Generalization to other correlated system s which can be described with the Luttinger liquid model, like metallic Carbon nanotube, is given.

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I. IN TRODUCTION

It is now well known that the uctuations of electric current contain valuable information both on the discreetness of the charge and on the quantum properties of transport [1, 2, 3, 4]. Many studies of these uctuations, both experimental and theroretical, have been done on systems in a stationary regime, with constant or tim e-periodic voltage biases. W e consider here a nonstationnary problem, where a voltage pulse is used to in ject a given charge in a conductor, and call this process \tim e-controlled charge in jection". Such a real-tim e transfer of charge m ight prove of great interest for applications, for example as a tool for the transfert of information. The current uctuations also play an important role in the problem of time-controlled charge injection, as these uctuations should be made as low as possible to transfer the charge as precisely as possible.

An interesting area to study tim e-controlled charge injection consists of conductors with strongly correlated electrons. Indeed, in these systems, the elementary excitations are collective electronic excitations, and m ay have a charge e which is only a fraction of the \elementary" charge e. W e will be particularly interested in edge states of the fractional quantum Halle ect (FQHE) for Laugh hin fractions, where elementary excitations have a charge e = e = (2n + 1), with n an integer (the most accessible) charge being e = e=3) [5, 6, 7]. This problem is interesting on its own from a theoretical perspective, as it allows to see how a system with strongly correlated electrons behaves in a non-stationary setup. It is also interesting for potential experim ental applications, as the injection of a well controlled charge, e.g. a unique electron, in an edge state of the FQHE is an important experimental challenge, which could prove an useful tool in the quantum information domain for example.

In the case where electrons are uncorrelated (norm al metal conductors), this problem has been studied by Levitov and coworkers [8]. De ning the Faraday ux

= $e^{-\kappa_1}$ dtV (t), they have shown that the mean transm itted charge hQ i is sim ply proportional to the ux (O hm 's law), hQ i , but that the charge uctuations hQ² i are in general logarithm ically divergent, except for \integer" values of the ux = 2 n (with n an integer) where these uctuations are nite. They have related this behavior to the A nderson orthogonality catastrophe [9]. The goal of this report is to study this problem in the case where the charge is transfered into an edge state of the FQ HE, orm ore generally in a chiral Luttinger liquid.

The setup of this paper is as follows. The system is described in section II. In section III, we consider the case of the pertrubative regime, where the tunneling between the norm alm etal and the edge state is low. The convergence of the mean charge and of its uctuations is studied, and explicit form ull are given within the adiabatic approximation, whose validity is con med by numerical calculations. In section IV, we give non-perturbative results for the special case of electron tunneling in an edge state of the FQHE with lling factor = 1=3. Finally, in section V, some perspectives are discussed, like the relevance of our results for other systems, and conclusions are given.

II. DESCRIPTION OF THE SYSTEM

The system we consider is composed of a norm alm etal (non-interacting electrons, with Ferm i liquid behavior) close to an edge state of a 2D electron gas in the FQ HE regime. A voltage pulse V (t) is applied between the two conductors, which leads to the tunneling of electrons. The FQ HE regime is characterized by the lling factor = 1=m, where m is an odd integer. Note that the case m = 1 correspond to the integer quantum Hall e ect, where there are no correlations between electrons and the edge state describe a Ferm i liquid. We expect thus to recover, when we take = 1, the results of Levitov et



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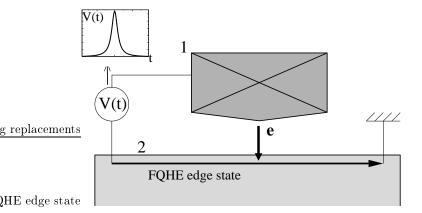


FIG.1: The setup: electron tunneling between a usual conductor and an edge state of a 2D electron gas in the fractional quantum H all e ect (FQHE) regime, induced by a time dependent voltage V (t).

al.

W e call $_1$ ($_2$) the electron annihilation operator at the tunneling point in conductor 1 (conductor 2, the edge state) - see Fig.1. U sing Peierls' substitution to have the voltage pulse as a vector potential only, we have the follow ing tunneling H am iltonian between the two conductors:

$$H_{T}(t) = -v_{F} e^{i(t)} y_{1}(t) z(t) + h.c.$$
 (1)

where is the tunneling amplitude and (t) = $e^{-N_t}_{1} dt^0 V (t^0)$ is the time-dependent Faraday ux. Similarly, the tunneling current is given by:

$$I_{T}(t) = iev_{F} e^{i(t)} \frac{y}{1}(t) \frac{z}{2}(t) h.c.$$
 (2)

The quantities we need to calculate are the mean transmitted charge hQ i:

$$hQi = \begin{array}{c} 2 \\ d \\ 1 \end{array} hF_{\rm T} ()i \qquad (3)$$

and its uctuations h $Q^2 i = hQ^2$ hQ fi:

$$Q^{2} = dt I(t) dt^{0} I(t^{0}) hQ^{2} I(t^{0}) dt^{0} I(t^{$$

The system being out of equilibrium, we use the K eldysh form alism, introducing a time contour going st from 1 to +1 (upper branch, = +1) and then going back from +1 to 1 (lower branch, = 1), and using the time ordering operator T_K along this contour [10].

III. PERTURBATIVE RESULTS

A. Form alism

In this section, we will calculate the mean transmitted charge and its uctuations in the tunneling regime, where

! 0. This allows us to get the results by calculating only the lowest order in the tunneling am plitude . Note that ! 0 ensures the system is in the tunneling regime for any nite value of V (t). Indeed, for electron tunneling from a norm alm etal to an edge state of the FQHE with

ling factor = 1 = (2p + 1), one has in the tunneling lim it the tunneling current I ${}^{2}j!_{0}j^{2} = {}^{1}$, where $!_{0}$ is proportionnal to the applied voltage V. As 2 = 1 > 0, it is clear that when V (t) ! 0 the tunneling current goes to 0 and can thus be calculated perturbatively. Note that the situation would be di erent for tunneling of fractionally charged excitations between two edge states of the same FQHE uid, where V ! 0 brings the system out of the tunneling regime

As we are considering the system in the tunneling regime, we can restrict ourselves to the lowest order contribution in the tunneling amplitude \cdot At order ², we have for the mean transmitted charge:

U sing Eqs. (1) and (2), with standard properties of the K eldysh G reen functions, and parity properties, we can write this expression as:

$$hQ i = 2e \gamma_{F}^{2} \stackrel{2}{\xrightarrow{2}} dt \quad d \quad Im \ (G_{1}(t)G_{2}(t))$$

$$1 \quad 1$$

$$sin ((+ t=2) (t=2)) \quad (6)$$

where $G_i(t)$ is the standard G reen_Efunction for conductor i (i = 1;2): $G_i(t) = T_i^y(0)_i(t)$. Sim ilarly, we get for the charge uctuations (Eq. (4)):

$$Q^{2} = 2e^{2}v_{F}^{2} \xrightarrow{2} dt d Re(G_{1}(t)G_{2}(t))$$

$$\sum_{1 = 1}^{1} [\cos((t + t=2)) (t=2)) 1] (7)$$

Note that the term $\-1"$ next to the cosine has been introduced to regularize the expression. This regularizing term is needed because we have permuted the order of the t and integrals, and is not needed if the t integral is performed before the integral, as dtR e (G₁(t)G₂(t)) = 0.

B. Convergence of the integrals

Eqs. (6) and (7) will allow us to study the properties of the charge injection. On these formul, we see that both the injected charge and its uctuations are obtained with two elements: the G reen functions product G₁(t)G₂(t), which contains all the inform ation about the two conductors, and a kernelobtained by integrating over

a function of the Faraday ux (t), which contains all the information about the voltage pulse V (t). To study the convergence/divergence of the time integrals for the charge and its uctuations, we need the time behavior of these two elements. Note that as we consider tunneling through a single point contact, the normal metal can be m apped [12] to a chiral Luttinger liquid with parameter = 1. The G meen functions at zero tem perature are simply [10]:

$$G_{1}(t) = \frac{1}{2 a} (1 + iv_{F} t=a)^{-1} \qquad G_{2}(t) = \frac{1}{2 a} (1 + iv_{F} t=a)$$
(8)

where a is a short length cuto , and = 1=m the lling factor of the FQHE conductor. Introducing K = (1=2)(1 + 1=), with K an integer, we see that the large time behavior of the real and imaginary part of $G_1(t)G_2(t)$ is:

Im
$$(G_1(t)G_2(t))$$
 t ^(2K + 1) Re $(G_1(t)G_2(t))$ t ^{2K}
(9)

(the imaginary part does not contain a t 2K term as this term includes a sin (K) factor which is zero). We now turn to the large time behavior of the kernels involving the_{R1}ux (t). For the mean charge, it is given by B₁(t) = $_1$ d sin ((+t=2) (t=2)). By hypothesis, the voltage pulse V (t) is important only in a nite time domain, of width t. This means that for t t, and for a interval of the order of t, we have:

$$(+t=2)$$
 $(t=2) = \frac{e^{Z_{+t=2}}}{2} V(t)$
 $(\frac{t=2}{2}) \frac{e^{-Z_{-1}}}{2} V(t) = (10)$

We have thus $B_1(t)$ ' $\sin()t + C_1$ for t ! 1, where C_1 is a constant. Similarly, we have for the kernel of the charge uctuations, $B_2(t) = \frac{1}{1} d \left[\cos((+ t=2) (t=2)) 1\right]$, 2B(t) ' ($\cos()$ 1)t + C₂. Both the kernels $B_1(t)$ and $B_2(t)$ have thus a linear dependence in t for large t, except for the special values of the ux = 2 n (with n 2 N) where they are constant for large t.

C om bining the large time behavior of the G reen functions and of the kernels, we see that the integrand for the m ean charge (Eq. (6)) behaves for large t as:

$$B_1$$
 (t) Im (G_1 (t) G_2 (t)) ' sin ()t 2K + C_1 t $^{2K+1}$ (11)

while for the charge uctuations (Eq. (7)) we have:

$$B_2$$
 (t) Re (G₁ (t)G₂ (t)) ' (cos() 1)t^{2K + 1} + C₂t^{2K}
(12)

Let us rst check that this is compatible with the known results for non-interacting electrons. In this case, one has = 1 and thus K = 1. We see then that the mean charge integral is always converging, while the charge uctuations integral has a logarithm ic divergence, except for = 2 n, and we recover thus the results of Levitov et

al. [8]. Turning now to interacting electrons, one has = 1=m with m > 1 an odd integer, and thus K is an integer with K > 1. In this case, we see that the m ean charge integral is as before always converging, and that the charge uctuations integral is also always converging, independently of the value of the ux ! This m eans that, because of the electronic correlations, the divergence of the charge uctuations is rem oved.

C. Explicit form ul and the adiabatic approximation

1=

It is possible to go further and to get explicit form ul for the integrals of the m ean injected charge and its uctuations. For simplicity, we will restrict ourselves to the case = 1=3, but the results shown here can be extended to any value of = 1=(2n + 1). For = 1=3, the G reen function product is:

$$Re (G_{1} (t) G_{2} (t)) = \frac{1}{4^{2}a^{2}} \frac{1}{(1 + (v_{F} t=a)^{2} + (v_{F} t=a)^{4})^{4}}{(1 + (v_{F} t=a)^{2})^{4}}$$

Im (G_{1} (t) G_{2} (t)) = \frac{1}{4^{2}a^{2}} \frac{4 (v_{F} t=a) (1 - (v_{F} t=a)^{2})}{(1 + (v_{F} t=a)^{2})^{4}} (13)

Let us rst consider the integral for the m ean transm itted charge (Eq. (6)), which involves the imaginary part of the G reen function product. On Eq. (13), we see that this part is important in a time domain of the order of $a=v_F$, and then quickly decreases to 0 fort $a=v_F$ as t^{-5} . For the t integral giving the m ean transm itted charge, we can thus consider that times up to t $a=v_F$ only contribute importantly to the integral. In the kernel B₁ (t), time t appears in the bounds t=2 of the V (t) integral in the sinus. As the short time cuto $a=v_F$ is much smaller that the typical time of variation of V (t⁰), the function V (t⁰) can be considered as constant in this integral, giving sin (e=~V () t). The m ean charge is then:

$$hQi = (1)2ev_{F}^{2} \stackrel{2}{\overset{2}{\xrightarrow{}}} d dt sin - \frac{e}{\overset{2}{\xrightarrow{}}} V()t$$

$$\lim_{1 \to 1} (G_{1}(t)G_{2}(t)) (14)$$

The t integral in (14) is simply the form ula for the mean tunneling current when a constant voltage V () (with a given) is applied. We have thus perform ed an adiabatic approximation, valid because of the rapid decrease of the G reen function product. Performing the time integral, using Eq. (13), we get the result:

$$hQ i = \frac{e^{-2}a^2}{2 - 3k_F^2} \int_{-1}^{Z_{+1}} d \frac{e}{-} V(r)^3$$
(15)

We see that the mean transmitted charge is not proportional to the total ux , but rather to the integral of PSIrag replacements a voltage pulse of given shape whose ux is varied by an overall scale factor only, the mean transmitted charge varies as the cube of the ux . This behavior is a consequence of the non-linear relation between voltage and current for tunneling in a Luttinger liquid. The presence of the cuto a in the form ula is typical of electron tunneling in a Luttinger liquid. Note that for another lling factor = 1=m, the result would be proportional to the integral of (V ())^m.

Turning now to the charge uctuations, one could expect to obtain similar results: from Eq. (13), we see that the real part of the product of the G reen functions is important for t $a=\psi$ only, and decreases rapidly to 0 as t⁴. However, when V () is not large enough the adiabatic approximation breaks down, because $_{1}^{R+1}$ dtRe(G₁(t)G₂(t)) = 0, which means that the contribution of the time intervalup to t $a=\psi$ may vanish. We have thus to distinguish between two regimes, small ux 1 and large ux.

For the small regime let us consider a voltage pulse $V_R(t) = V_1(t)$, where $V_1(t)$ is of xed shape and unit ux (dtV₁(t) = 1), and 1. The cosine in the kemel of the charge uctuations $B_2(t)$ can then be developped at second order, giving $\frac{(1)}{2}^2 = \frac{R_1 + t=2}{t=2} dt^0 V_1(t^0)^2$. When we vary the ux corresponding to the voltage pulse V (t), we see that the kemel $B_2(t)$, and thus the charge uctuations, varies as 2^2 . The charge uctuations are thus proportional to 2^2 for small , contrarily to the m ean transmitted charge which varies as 3^3 .

In the other regime, with a larger ux, we can use the same adiabatic approximation as for the mean charge. We get:

$$Q^{2} = 2e^{2}v_{F}^{2} \overset{2}{\xrightarrow{}} dt Re (G_{1} (t)G_{2} (t))$$

$$Z^{1}_{+1} h \qquad i$$

$$d \cos \frac{e}{-}V ()t \qquad 1 \qquad (16)$$

Permuting the t and integrals (the $\-1$ " term does not contribute then), we see that for V (t) large enough the variations of the cosine are rapid enough to get a nonzero integral on the dom ain where the G reen functions are important (t a). Perform ing the t integral, we get for the charge uctuations, for large :

$$Q^{2} = \frac{e^{2} a^{2} a^{2}}{2 3 k_{F}^{2}} d \frac{e}{v} (t)^{3}$$
 (17)

In this regime, we recover for the charge uctuations a behavior similar to the one of the mean charge, with a dependence as ³ for a voltage pulse of given shape. Comparing Eqs. (15) and (17), we see that the charge uctuations are simply e times the mean charge. This

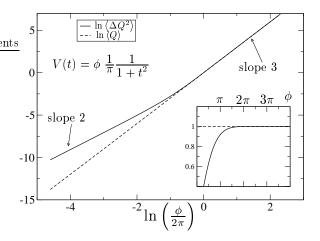


FIG.2: Results of the num erical integration of Eqs. (6) and (7), for a pulse of Lorentzian shape (V (t) = $(1 =)(1 + t^2)^{-1}$). Mean transmitted charge (dashed curve) and its uctuations (full curve) as a function of , on a log-log plot. The mean charge has a slope 3, while the charge uctuations has a slope 2 for sm all and a slope 3 for large . Inset: ratio between the results of the adiabatic approxim ation (Eqs. (15) and (17)) and num erical integration of Eqs. (6) and (7), for the mean charge (dashed line) and its uctuations (full line). The adiabatic approxim ation (full line). The adiabatic approxim ation is clearly valid for the mean charge, while it is valid for the charge uctations when & 2.

m eans that for larger ux, although the system is nonstationary, the charge uctuations have a poissonian character, as is common in time-independent problem s.

To con m the results obtained with the adiabatic approximation, we have performed a numerical integration of Eqs (6) and (7). The results for the case of a Lorentzian voltage pulse, V (t) = $(1=)(1+t^2)^{-1}$ are shown on Fig. 2. On this gure, it is clear that the mean transmitted charge behaves as 3 for all , while the charge uctuations behaves as 3 for large , but as 2 for small . The inset of Fig. 2 shows the ratio between the num erical integrations and the results of the adiabatic approximation, Eqs. (15) and (17); we see that the adiabatic approximation gives excellent results for hQ i for all uxes , while it gives excellent results for h Q²i & 2 . Num erical integration with other shapes when of voltage pulses (not shown) gives sim ilar results.

IV. NON PERTURBATIVE RESULTS

In the previous section, we have shown that, except for the charge uctuations at small , we obtain a very good approximation of the exact results by using an adiabatic approximation, where the transmitted charge due to the voltage pulse V (t) is computed by integrating over t the stationnary current I_{st} due to V = V (t). As the adiabatic approximation is related to the rapid decrease of the G reen function product G_1 (t) G_2 (t), and as higher orders of the tunneling current in ply higher powers of this product, we expect the adiabatic approximation to be valid in the non-perturbative regime. We will thus compute non-pertubative results for the mean charge and its uctuations starting from non-pertrubative results for the stationnary tunneling current and noise. Because this method im plies the calculation of stationnary current only, it is much simpler than the full calculations.

Non-perturbative results for the stationnary current are known in the case of tunneling of electrons from a norm alm etalto an edge state of the FQHE with lling factor = 1=3. Indeed, for tunneling properties, this system is equivalent to the tunneling of electrons between two edges states of the same quantum Hall uid with = 1=2, as shown in [11]. This equivalence can be guessed from Eq. (8): the G reen function product is G_1 (t) G_2 (t) = (2 a) 2 (1 + iv_F t=a) $^{(1+1=v)}$, which for = 1=3 is the same as (2 a) 2 (1 + iv_F t=a) $^{1=v^{0}}$ (1 + iv_F t=a) $^{1=v^{0}}$ with $v^0 = 1=2$. In [11], non-perturbative results for the tunneling current and noise are obtained for this system, as it is linked by the duality symmetry to the tunneling of fractionnaly charged excitations (with e = e=2) between two = 1=2 edge states, which can be treated non-perturbatively by referm ionization.

U sing results of [11], we have for the stationnary tunneling current, $I_{\rm st},$ corresponding to voltage V :

$$I_{st} = \frac{e^2}{4} V \qquad \frac{e v_F}{4} A \arctan \frac{e V}{-v_F} a \qquad (18)$$

This expression shows there are two extrem e regimes for the current. For V or ! 1, the tunneling is made through a barrier of large transparency, and the current goes to the maximal value $e^2V = (2h)$. On the opposite, for V or ! 0, the barrier transparency goes to 0, and we recover the perturbative results with I $^2V^3$. To get the mean charge transmitted with a voltage pulse pulse V (t), we now simply integrate over t the current I_{st} corresponding to V (t). This gives:

$$hQ i = \frac{e}{4} \qquad \int_{1}^{2} \frac{1}{4} \frac{ev_F}{4a} \operatorname{Arctan} \frac{eV(t)}{-v_F} a \qquad (19)$$

In the tunneling regime, ! 0, we recover the expression (15) obtained perturbatively, where the mean charge varies as ³. Note that we obtain the same expression for the lim it of very small voltage V (t) for any given if V (t) 1 for all t. On the opposite, in the lim it of a large or large V (t), the charge becomes simply proportionnal to the ux. The system shows thus a crossover between hQ i ³ at low and hQ i at large , the position of the crossover being a monotonic decreasing function of .

We now turn to the charge uctuations. Using again the results of [11], we get the following expression for the non-perturbative stationnary current noise S_{st} due to voltage V, with $x = (eV = \sim v_F)$ a:

$$S_{st} = \frac{e^2 v_F}{4 a}$$
 A rctan (x) $\frac{x}{1 + x^2}$ (20)

For V or ! 0, we recover the tunneling regime, with S = eI ²V³. As for the current, we obtain the charge uctuations h Q² i due to a voltage pulse V (t) by integrating over t the noise S_{st} corresponding to V = V (t). De ning x (t) = (eV (t)=~v_{F}) a, we get

$$Q^{2} = \frac{e^{2} v_{F}}{4 a} \int_{1}^{Z_{1}} dt A rctan (x (t)) \frac{x (t)}{1 + x (t)^{2}}$$
(21)

There is also a crossover in the behavior of h Q^2 i as a function of : when is small, we recover the results of Eq. (17) with hQ²i ³. As we know from the previous section, the adiabatic approximation does not reproduce in this case the correct 2 behavior for ! 0. W hen is large it is more di cult to get analytically the behavior ofh Q²i(); num erical integration for di erent types of V (t) shows that h Q^2 i ¹⁼ⁿ when V (t) tⁿ for t! 1. This dependance on the asymptotic properties of V (t) com es from the fact that for large , noise com es mainly from the tregions where V (t) is small (otherwise the barrier has a high transparency and noise is sm all), which are simply the tails of the voltage pulse.

V. PERSPECTIVES AND CONCLUSIONS

The results we have obtained so far are valid for electron injection in any chiral Luttinger liquid, and can be applied to other systems than edge states of the fractional quantum Halle ect. In particular, the conduction electrons in a single-wall metallic C arbon nanotube can be described in terms of di erent modes of chiral Luttinger liquids. The electronic G reen function in such a nanotube can be shown to be [13, 14]:

$$G_2$$
 (t) = (2 a) 1 (1 + iv_F t=a) with $= \frac{3}{4} + \frac{1}{8} g + g^{-1}$
(22)

where g is the parameter characterizing the interactions in the nanotube (typical experimental values are in the range [0.2;0:3]). Note that > 1, but is not an integer. W e can then repeat, mutatismutandis, the same reasoning as in section III to study the mean charge and its

uctuations. We de ne K = (1=2)(1 +), with K > 1. As K is not an integer, the large time behaviors of the real and in aginary part of G₁ (t) G₂ (t) are here the same:

Im
$$(G_1(t)G_2(t))$$
 t^{2K} Re $(G_1(t)G_2(t))$ t^{2K}
(23)

Repeating the reasoning that leads to Eqs. (11) and (12), we see that because K > 1, both the mean charge and its uctuations are nite, independently of the value of the ux (and thus of V (t)). As for an edge state of the FQHE, the electrons correlations in a nanotube prevent the divergence of the charge uctuations for non-stationary injection.

Our results can also be of interest for the very general case of non-stationnary electron tunneling between two norm alm etals, when an Ohm ic in pedance is present in the system. Indeed, it is known that a mapping exists between a coherent one-channel conductor coupled to an Ohm ic environment (the dynam ical C culom b blockade problem [15]) and a Luttinger liquid with an impurity [16]. Our results suggest then that the divergence of charge uctuations as predicted by Levitov and coworkers [8] are suppressed by the coupling to an Ohm ic environment, as this coupling can be mapped to electron interaction leading to Luttinger liquid behavior.

To conclude, we have shown that for the nonstationnary charge injection from a normal metal into a chiral Luttinger liquid, using a voltage pulse V (t), the electronic correlations in the Luttinger liquid prevent the charge uctuations from being divergent for a generic voltage pulse. In the perturbative regime with respect to the tunneling am plitude, we have shown that explicit form ul for the mean injected charge and its uctuations can be obtained using an adiabatic approximation. We have identied when this adiabatic approximation breaks down, and shown that when it is valid, it leads to a Schottky-like relation bewteen the charge and its

uctuations. Finally, we have obtained non-perturbative results for the special case of charge injection in an edge state of the FQ HE with lling factor = 1=3. Centre de Physique Theorique is UMR 6207 du CNRS, associated to Universite de la M editerann ee, Universite de Provence and Universite de Toulon.

- [1] Y M .B lanter and M .Buttiker, Phys.Rep. 336, 1 (2000).
- [2] T. Martin in Les Houches Summer School session LXXX L, edited by E.Akkermans, H.Bouchiat, S.Gueron and G.Montam baux (Springer, 2005).
- [3] M.Reznikov, M.Heiblum, H.Shtrikm an and D.Mahalu, Phys.Rev.Lett. 75, 3340 (1995).
- [4] A.Kumar, L.Sam inadayar, D C G lattli, Y.Jin and B. Etienne, Phys. Rev. Lett. 76, 2778 (1996).
- [5] X.-G.Wen, Int.J.Mod.Phys.B 6, 1711 (1992).
- [6] L. Sam inadayar, D.C. G lattli, Y. Jin and B. Etienne, Phys. Rev. Lett. 79, 2526 (1997)
- [7] R. de Picciotto, M. Reznikov, M. Heiblum, V. Um ansky,
 G. Bunin, D. Mahalu, Nature (London) 389, 162 (1997).
- [8] L.S. Levitov, H. Lee and G.B. Lesovik, J. M ath. Phys. 37, 4845 (1996).

- [9] P.W . Anderson, Phys. Rev. Lett. 18, 1049 (1967)
- [10] C. de C. Cham on, D. E. Freed and X. G. W en, Phys. Rev. B 51, 2363 (1995).
- [11] N P. Sandler, C de C. Cham on and E. Fradkin, Phys. Rev. B 59, 12521 (1999)
- [12] C.deC.Cham on and E.Fradkin, PhysRev.B 56, 2012 (1997).
- [13] R.Egger and A.O.Gogolin, Eur. Phys. J.B 3, 281 (1998)
- [14] A. Crepieux, R. Guyon, P. Devillard and T. Martin, Phys. Rev. B 67, 205408 (2003).
- [15] G.-L. Ingold and Y.V. Nazarov, in Charge tunneling Rates is UltrasSmall junctions, B294, edited by H. Grabert and M.H. Devoret (Plenum, New York, 1992)
- [16] I.Sa and H.Saleur, Phs. Rev. Lett. 93, 126602 (2004)